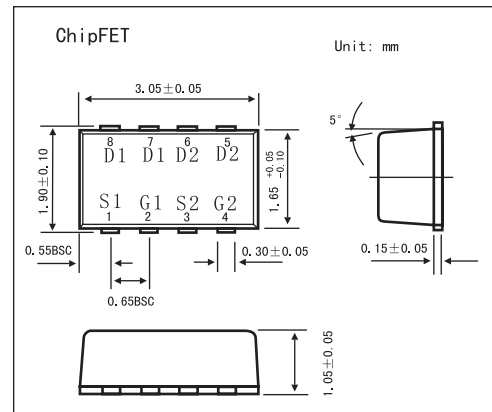
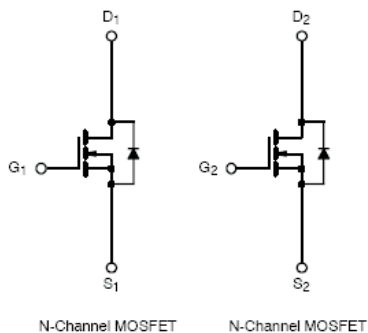


## Dual N-Channel 2.5-V (G-S) MOSFET KI5904DC

### ■ Features



### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	5secs	Steady State	Unit
Drain-Source Voltage	$V_{DS}$	20		V
Gate-Source Voltage	$V_{GS}$	$\pm 12$		
Continuous Drain Current ( $T_J = 150^\circ\text{C}$ ) $T_A = 25^\circ\text{C}$ $T_A = 85^\circ\text{C}$	$I_D$	$\pm 4.2$	$\pm 3.1$	A
		$\pm 3.0$	$\pm 2.2$	
Pulsed Drain Current	$I_{DM}$	$\pm 10$		
Continuous Source Current (Diode Conduction)*	$I_S$	1.8	0.9	
Maximum Power Dissipation * $T_A = 25^\circ\text{C}$ $T_A = 85^\circ\text{C}$	$P_D$	2.1	1.1	W
		1.1	0.6	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to 150		$^\circ\text{C}$
Soldering Recommendations		260		$^\circ\text{C}$

\*Surface Mounted on 1" X 1" FR4 Board.

### ■ Thermal Resistance Ratings

Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient *	$R_{thJA}$	$t \leq 5 \text{ sec}$	50	60	$^\circ\text{C}/\text{W}$
		Steady-State	90	110	
Maximum Junction-to-Foot (Drain)	$R_{thJF}$	30	40		

\* Surface Mounted on 1" X 1" FR4 Board.

## KI5904DC

## ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 \mu A$	0.6			V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0 V, V_{GS} = \pm 12 V$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 16 V, V_{GS} = 0 V$			1	$\mu A$
		$V_{DS} = 16 V, V_{GS} = 0 V, T_J = 85^\circ C$			5	
On-State Drain Current*	$I_{D(on)}$	$V_{DS} \geq 5 V, V_{GS} = 4.5 V$	10			A
Drain Source On State Resistance*	$r_{DS(on)}$	$V_{GS} = 4.5 V, I_D = 3.1 A$		0.065	0.075	$\Omega$
		$V_{GS} = 2.5 V, I_D = 2.3 A$		0.115	0.143	
Forward Transconductance <sup>b</sup>	$g_{fs}$	$V_{DS} = 10 V, I_D = 3.1 A$		8		S
Schottky Diode Forward Voltage*	$V_{SD}$	$I_S = 0.9 A, V_{GS} = 0 V$		0.8	1.2	V
Total Gate Charge	$Q_g$	$V_{DS} = 10 V, V_{GS} = 4.5 V, I_D = 3.1 A$		4	7.5	nC
Gate-Source Charge	$Q_{gs}$			0.6		
Gate-Drain Charge	$Q_{gd}$			1.3		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 10 V, R_L = 10 \Omega, I_D = 1 A, V_{GEN} = 10 V, R_G = 6 \Omega$		12	18	ns
Rise Time	$t_r$			35	55	
Turn-Off Delay Time	$t_{d(off)}$			19	30	
Fall Time	$t_f$			9	15	
Source-Drain Reverse Recovery Time	$t_{rr}$	$I_F = 0.9 A, di/dt = 100 A/\mu s$		40	80	ns

\* Pulse test :Pulse width  $\leq 300 \mu s$ , duty cycle  $\leq 2\%$